A Study of High Power Pulsed Characteristics of Low-Noise GaAs MESFETs (1981 [MWSYM])

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Low-noise GaAs MESFET's have been investigated for catastrophic burn-out ratings when exposed to representative pulses from an X-band transmitter/T-R cell combination. Also reported are failure analyses, non-catastrophic but recoverable effects and longer term tests.

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